

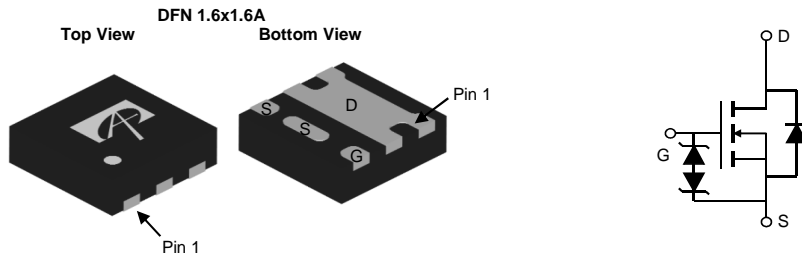
**General Description**

The AON1620 combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ . This device is ideal for load switch and battery protection applications.

**Product Summary**

$V_{DS}$	12V
$I_D$ (at $V_{GS}=4.5V$ )	4A
$R_{DS(ON)}$ (at $V_{GS}=4.5V$ )	< 22m $\Omega$
$R_{DS(ON)}$ (at $V_{GS}=2.5V$ )	< 27m $\Omega$
$R_{DS(ON)}$ (at $V_{GS}=1.8V$ )	< 36m $\Omega$

**Typical ESD protection** **HBM Class 2**



**Absolute Maximum Ratings  $T_A=25^\circ C$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	12	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Continuous Drain Current <sup>G</sup>	$I_D$	$T_A=25^\circ C$	4
		$T_A=70^\circ C$	3
Pulsed Drain Current <sup>C</sup>	$I_{DM}$	16	A
Power Dissipation <sup>A</sup>	$P_D$	$T_A=25^\circ C$	1.8
		$T_A=70^\circ C$	1.15
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ C$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	56	70	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A,D</sup>		Steady-State	88	110

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	12			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =12V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			1 5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±8V			±10	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.4	0.7	1.0	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =5V	16			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A T <sub>J</sub> =125°C		18 23.5	22 29	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =3A		21	27	
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =2A		27	36	mΩ
		V <sub>GS</sub> =1.5V, I <sub>D</sub> =1A		35		mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =4A		25		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.65	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				2.5	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =6V, f=1MHz		770		pF
C <sub>oss</sub>	Output Capacitance			180		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			130		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		1.2		Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g(4.5V)</sub>	Total Gate Charge	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =6V, I <sub>D</sub> =4A		8	12	nC
Q <sub>gs</sub>	Gate Source Charge			1		nC
Q <sub>gd</sub>	Gate Drain Charge			2		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =6V, R <sub>L</sub> =3.75Ω, R <sub>GEN</sub> =3Ω		2.5		ns
t <sub>r</sub>	Turn-On Rise Time			3.5		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			25		ns
t <sub>f</sub>	Turn-Off Fall Time			4		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =4A, di/dt=100A/μs		10		ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =4A, di/dt=100A/μs		3		nC

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The Power dissipation P<sub>DSM</sub> is based on R<sub>θJA</sub> t ≤ 10s value and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150° C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25° C.

D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to case R<sub>θJC</sub> and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

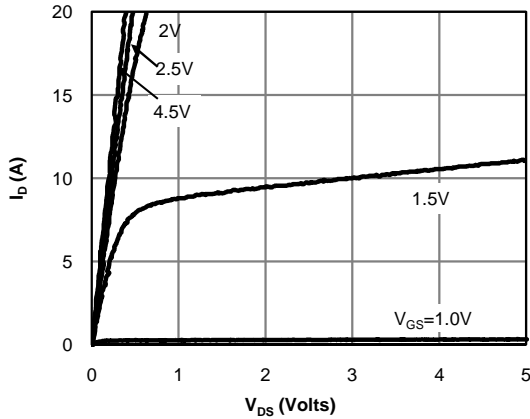
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

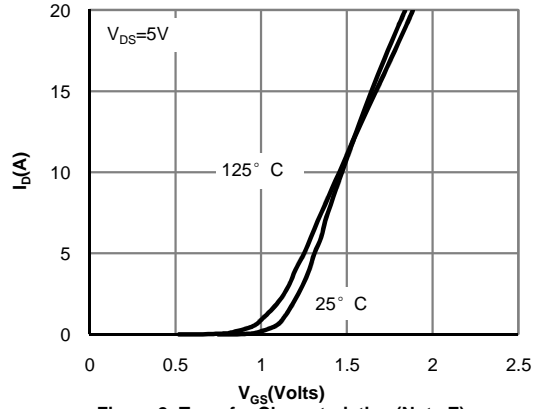
H. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C.

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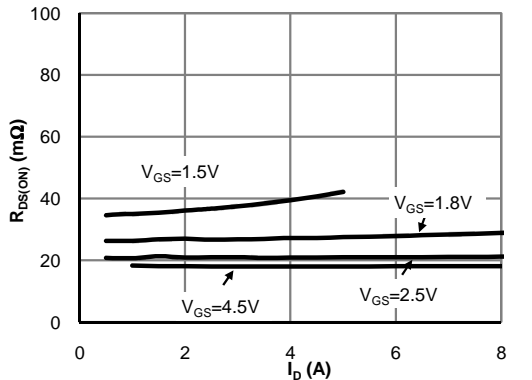
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



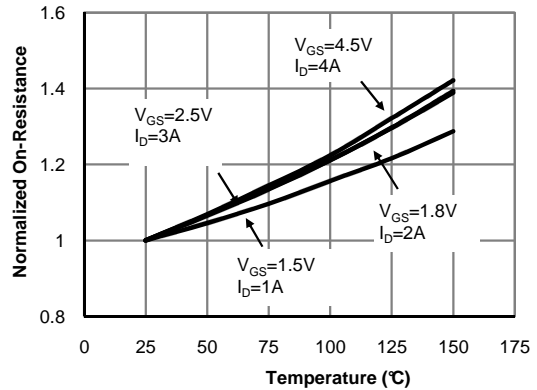
**Fig 1: On-Region Characteristics (Note E)**



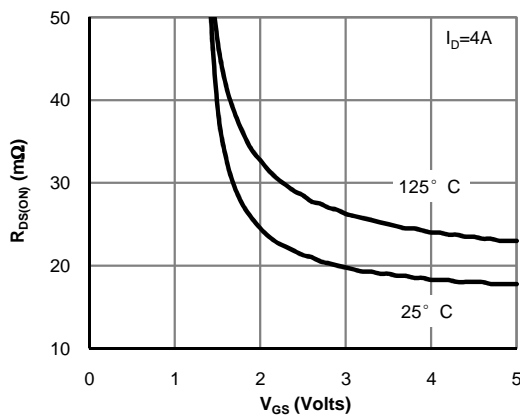
**Figure 2: Transfer Characteristics (Note E)**



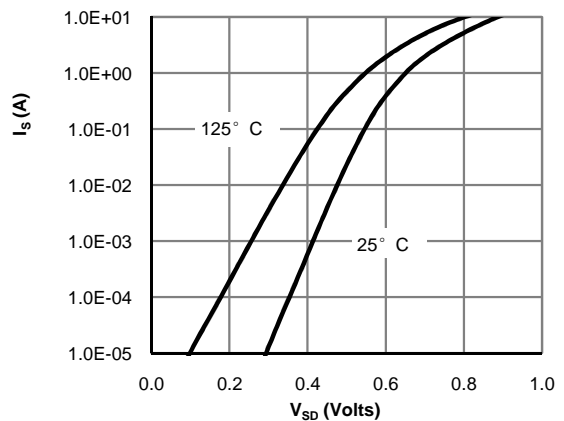
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)**



**Figure 4: On-Resistance vs. Junction Temperature (Note E)**

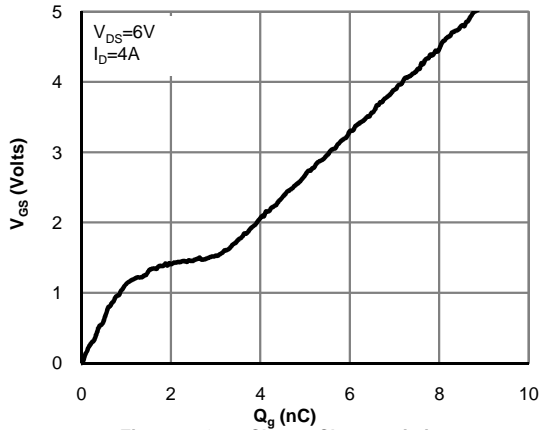


**Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)**

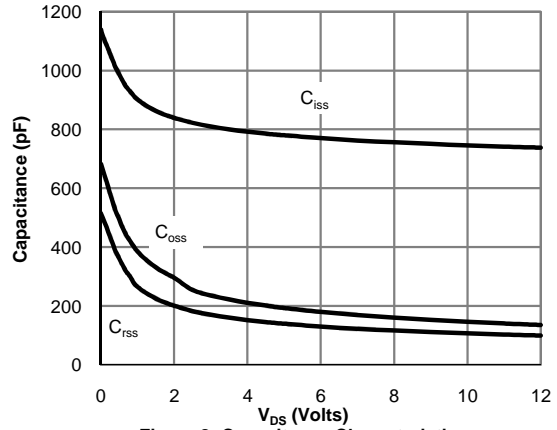


**Figure 6: Body-Diode Characteristics (Note E)**

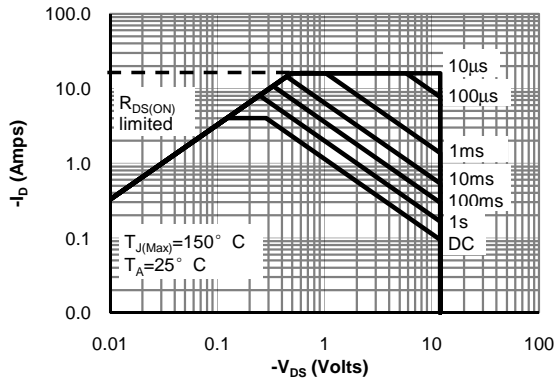
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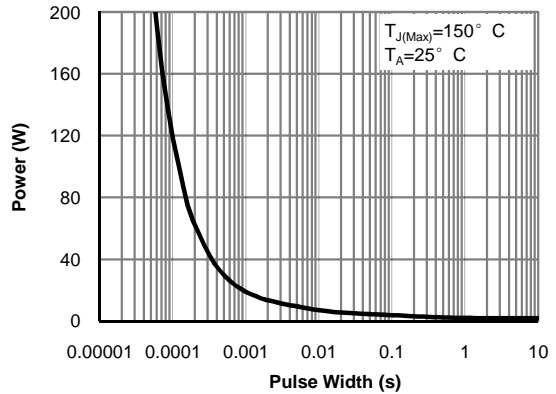
**Figure 7: Gate-Charge Characteristics**



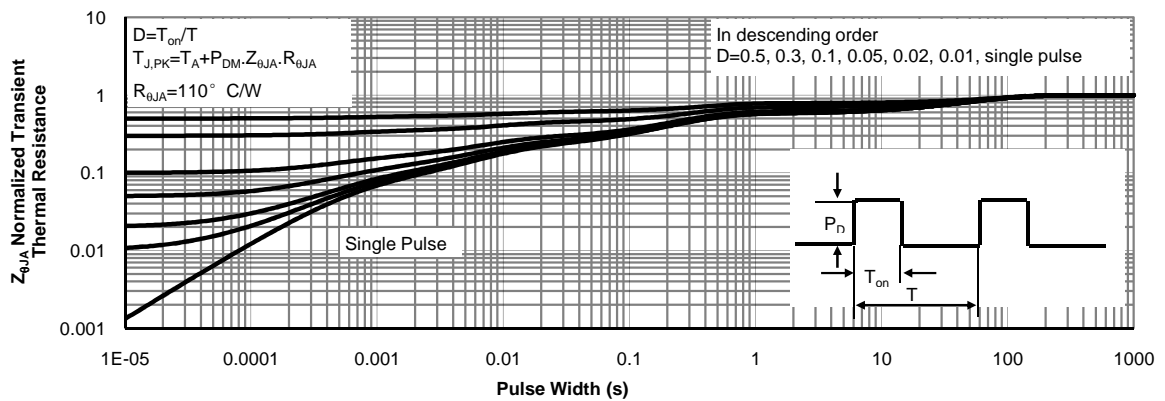
**Figure 8: Capacitance Characteristics**



**Figure 9: Maximum Forward Biased Safe Operating Area (Note F)**



**Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note H)**



**Figure 11: Normalized Maximum Transient Thermal Impedance (Note H)**

**Gate Charge Test Circuit & Waveform**



**Resistive Switching Test Circuit & Waveforms**



**Diode Recovery Test Circuit & Waveforms**

